

GENERAL PURPOSE HIGH FREQUENCY WIDE BAND IC FOR DOWN CONVERTER

DESCRIPTION

The μ PC1694GR is Silicon monolithic IC for down converter that is capable of operating up to 1 GHz.

This IC consists of double balanced mixer (DBM), local oscillator and IF amplifier. Furthermore, combination with the μ PC1663G (high-speed video amp) enables it to be applied to a FM demodulation circuit such as DBS tuner.

The package is 14 pin SOP suitable for smaller mounting area.

FEATURES

- Satisfactory 1% cross modulation distortion characteristics: $CM = 103 \text{ dB}\mu @ f_{des} = 200 \text{ MHz}$
- Wide band operation: $f \leq 1 \text{ GHz}$
- Low carrier leakage due to double balanced mixer (DBM)
- Easy to connect with varactor diode due to balanced amplifier oscillator
- Single-end push-pull IF amplifier suppresses fluctuation in output impedance
- Supply voltage: 5 V
- Packaged in 14 pin SOP suitable for smaller mounting area

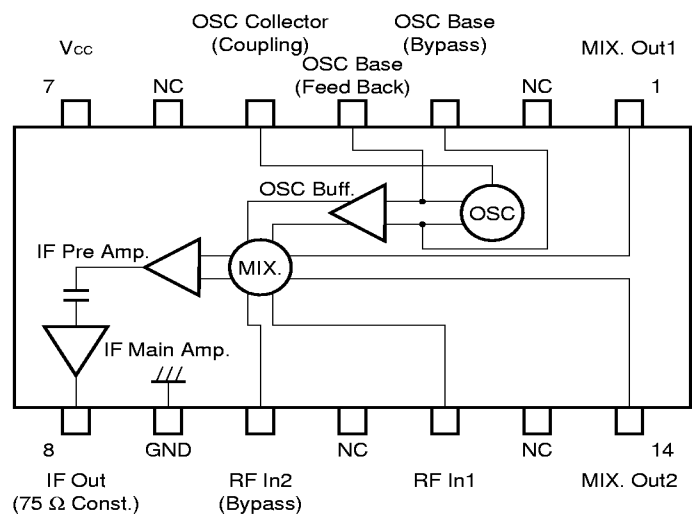
ORDERING INFORMATION

PART NUMBER	PACKAGE	PACKAGE STYLE
μ PC1694GR-E1	14 pin plastic SOP (225 mil)	Embossed tape 16 mm wide. Pin 1 indicates pull-out direction of tape.
μ PC1694GR-E2	14 pin plastic SOP (225 mil)	Embossed tape 16 mm wide. Pin 1 indicates roll-in direction of tape.

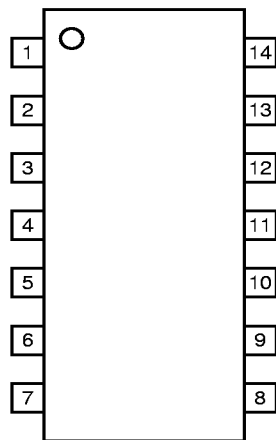
Remark For evaluation sample order, please contact your local NEC office.
(Part number for sample order: μ PC1694GR)

Caution: Electro-static sensitive devices

INTERNAL BLOCK DIAGRAM



PIN CONFIGURATION (Top View)



- 1. MIX output 1
- 2. GND (Non Connection)
- 3. OSC base (bypass)
- 4. OSC base (feedback)
- 5. OSC collector (coupling) (MIX/IF Amp. switch)
- 6. GND (Non Connection)
- 7. Vcc
- 8. IF output (75 Ω)
- 9. GND
- 10. RF input 2 (bypass)
- 11. GND (Non Connection)
- 12. RF input 1
- 13. GND (Non Connection)
- 14. MIX output 2

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

PARAMETER	SYMBOL	RATING	UNIT	TEST CONDITION
Supply Voltage	Vcc	6.0	V	
Power Dissipation	P _D	375	mW	T _A = 85°C ^{Note 1}
Operating Ambient Temperature	T _A	-40 to +85	°C	
Storage Temperature Range	T _{stg}	-65 to +150	°C	

Note 1. Mounted on 50 × 50 × 1.6 mm double copper clad epoxy glass board.

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{CC}	4.5	5.0	5.5	V

ELECTRICAL CHARACTERISTICS (T_A = 25°C, V_{CC} = 5 V)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Circuit Current 1	I _{CC1}	32	40	48	mA	No input signal ²
Mixer Output Voltage	V _{MIX}	-30	0	+30	mV	1-14 pin voltage, No input signal ²
Conversion Gain 1	CG1	14	18	21	dB	f _{RF} = 55 to 470 MHz, f _{IF} = 50 MHz P _{RF} = -40 dBm RF Input Terminal: Non Tuned ³
Conversion Gain 2	CG2	14	18	21	dB	f _{RF} = 470 to 890 MHz, f _{IF} = 50 MHz P _{RF} = -40 dBm RF Input Terminal: Non Tuned ⁴
Noise Figure 1	NF1	—	12.5	15.0	dB	f _{RF} = 55 to 470 MHz, f _{IF} = 50 MHz RF Input Terminal: Non Tuned ³
Noise Figure 2	NF2	—	13.5	16.0	dB	f _{RF} = 470 to 890 MHz, f _{IF} = 50 MHz RF Input Terminal: Non Tuned ⁴
Output Power 1	P _{O(sat)1}	+8	+10	—	dBm	f _{RF} = 470 MHz, f _{IF} = 50 MHz, P _{RF} = 0 dBm ³
Output Power 2	P _{O(sat)2}	+8	+10	—	dBm	f _{RF} = 890 MHz, f _{IF} = 50 MHz, P _{RF} = 0 dBm ⁴
Circuit Current 2 (U/IF)	I _{CC2}	32	40	48	mA	No input signal ²
Power Gain (U/IF)	G _P	17	21	24	dB	f _{in} = 50 MHz, P _{in} = -40 dBm ³
Noise Figure 3 (U/IF)	NF3	—	12.0	15.0	dB	f _{in} = 50 MHz ³

Note 2. On test circuit 1

Note 3. On test circuit 2

Note 4. On test circuit 3

STANDARD CHARACTERISTICS (FOR REFERENCE) ($T_A = 25^\circ\text{C}$, $V_{CC} = 5\text{ V}$)

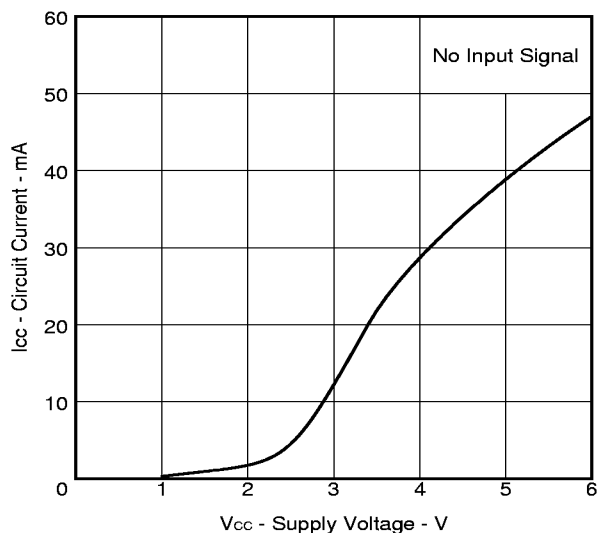
PARAMETER	SYMBOL	REFERENCE VALUE	UNIT	TEST CONDITIONS
Conversion Gain 3	CG3	24.5	dB	$f_{RF} = 55\text{ MHz}$, $f_{IF} = 50\text{ MHz}$, $P_{RF} = -40\text{ dBm}$ RF Input Terminal: Tuned ³
Conversion Gain 4	CG4	24.5	dB	$f_{RF} = 200\text{ MHz}$, $f_{IF} = 50\text{ MHz}$, $P_{RF} = -40\text{ dBm}$ RF Input Terminal: Tuned ³
Conversion Gain 5	CG5	23.0	dB	$f_{RF} = 470\text{ MHz}$, $f_{IF} = 50\text{ MHz}$, $P_{RF} = -40\text{ dBm}$ RF Input Terminal: Tuned ³
Conversion Gain 6	CG6	20.0	dB	$f_{RF} = 890\text{ MHz}$, $f_{IF} = 50\text{ MHz}$, $P_{RF} = -40\text{ dBm}$ RF Input Terminal: Tuned ⁴
1% Cross-modulation Distortion 1	CM1	103	dBμ	$f_{des} = 55\text{ to }470\text{ MHz}$, $f_{IF} = 50\text{ MHz}$ ^{3, 5}
1% Cross-modulation Distortion 2	CM2	100	dBμ	$f_{des} = 470\text{ to }890\text{ MHz}$, $f_{IF} = 50\text{ MHz}$ ^{4, 5}
1% Cross-modulation Distortion 3 (U/IF)	CM3	103	dBμ	$f_{des} = 50\text{ MHz}$ ^{3, 6}
Oscillation Frequency Stability 1	f_{stab1}	±100	kHz	$V_{CC} \pm 10\%$, $f_{osc} = 100\text{ to }520\text{ MHz}$ ³
Oscillation Frequency Stability 2	f_{stab2}	±200	kHz	$V_{CC} \pm 10\%$, $f_{osc} = 520\text{ to }940\text{ MHz}$ ⁴
Oscillation Stop (Start) Voltage 1	V_{osc1}	2.5	V	$f_{osc} = 100\text{ to }520\text{ MHz}$ ³
Oscillation Stop (Start) Voltage 2	V_{osc2}	3.0	V	$f_{osc} = 520\text{ to }940\text{ MHz}$ ⁴
Voltage Standing Wave Ratio	VSWR	1.3		$f_{IF} = 30\text{ to }60\text{ MHz}$

Note 5. $f_{undes} = f_{des} \pm 12\text{ MHz}$, $P_{in} = -31\text{ dBm}$, $f_{IF} = 50\text{ MHz}$, AM: 100 kHz, 30%Mod., S/I Ratio = 46 dBc, Output 75 Ω Open

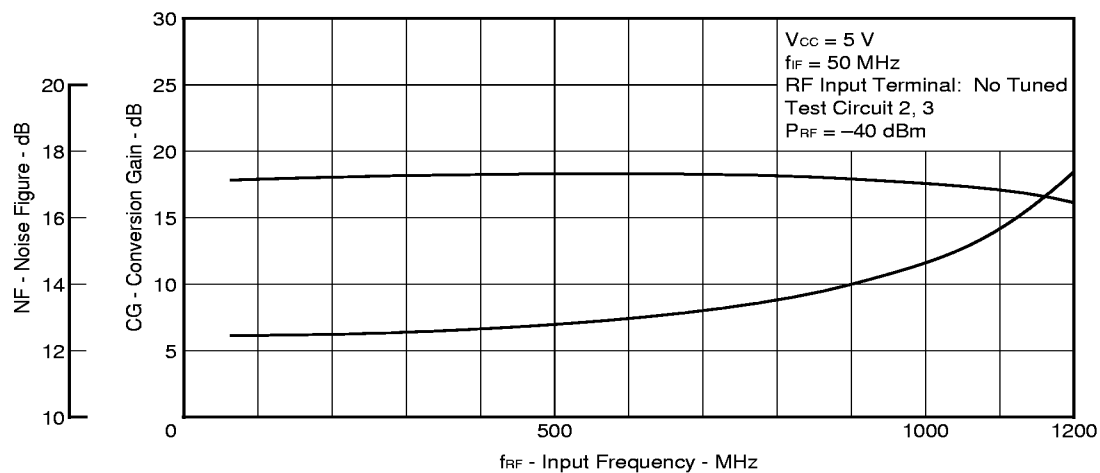
Note 6. $f_{des} = 50\text{ MHz}$, $f_{undes} = 62\text{ MHz}$, $P_{in} = -31\text{ dBm}$, AM: 100 kHz, 30% Mod., S/I Ratio = 46 dBc, Output 75 Ω Open

TYPICAL CHARACTERISTICS (T_A = 25°C)

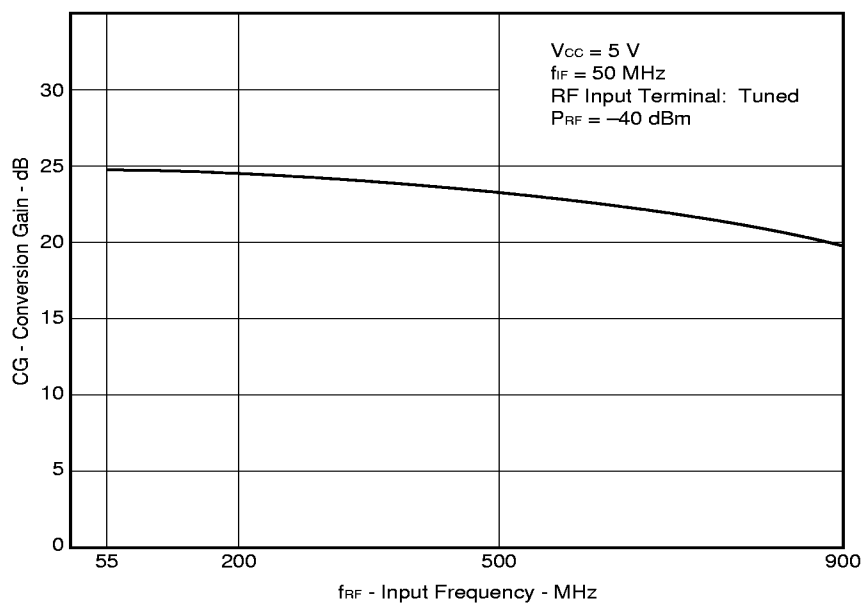
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



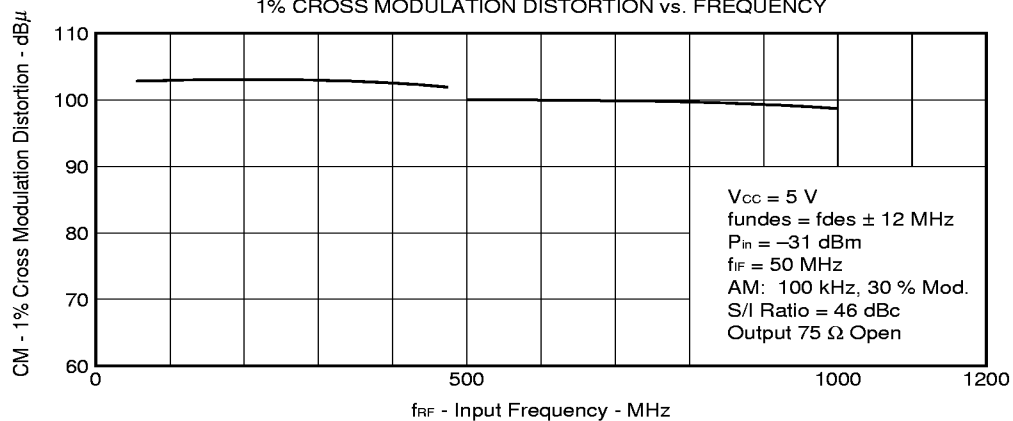
CONVERSION GAIN AND NOISE FIGURE vs. FREQUENCY

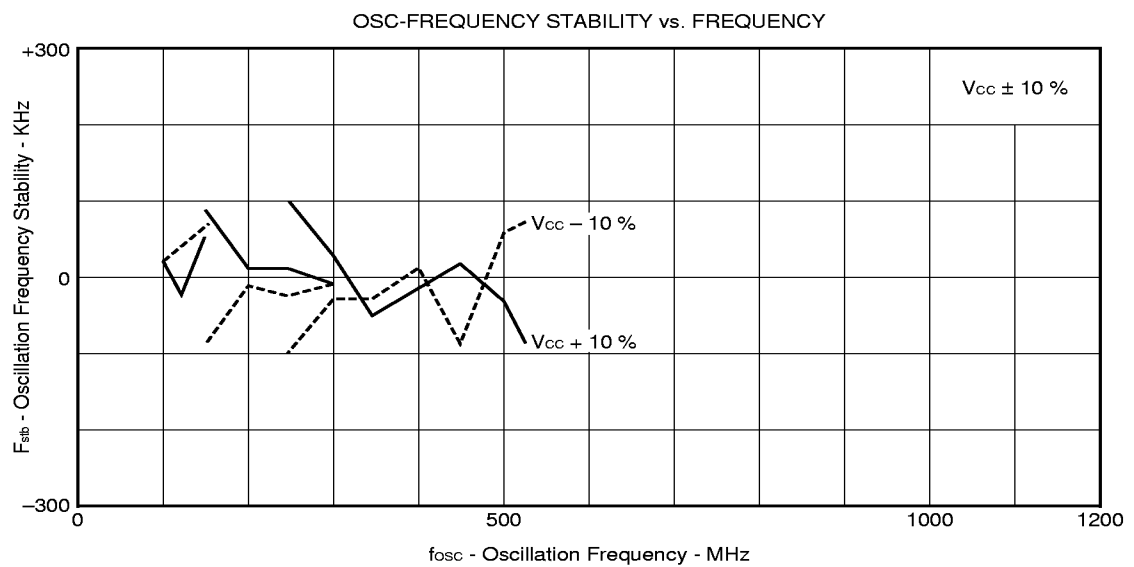
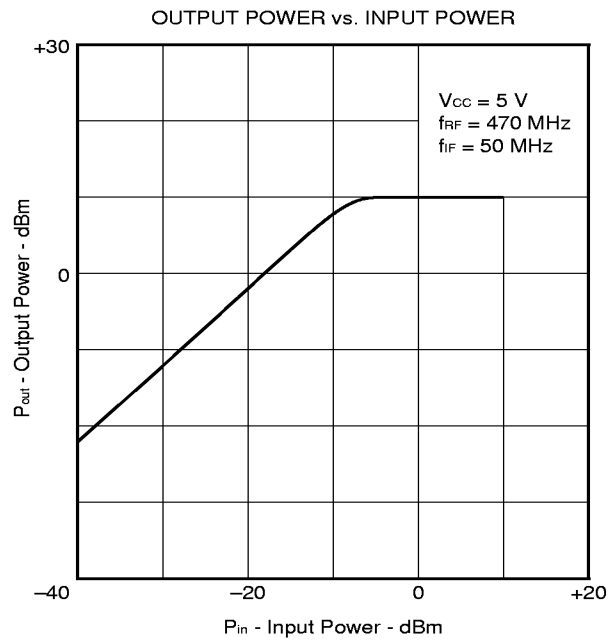


CONVERSION GAIN vs. FREQUENCY

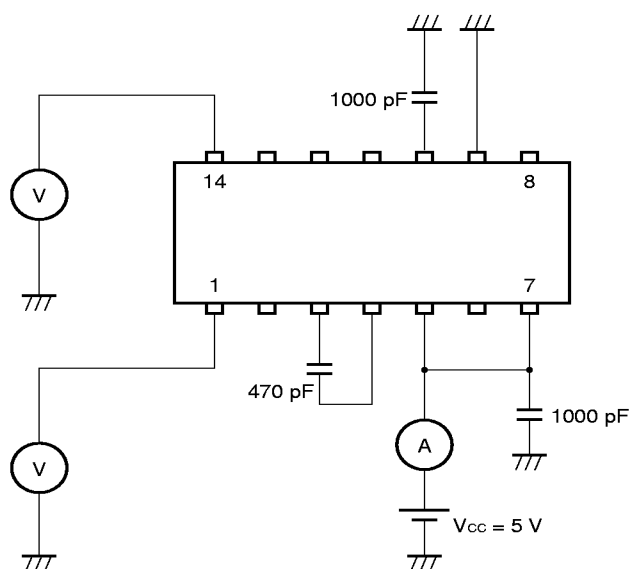


1% CROSS MODULATION DISTORTION vs. FREQUENCY



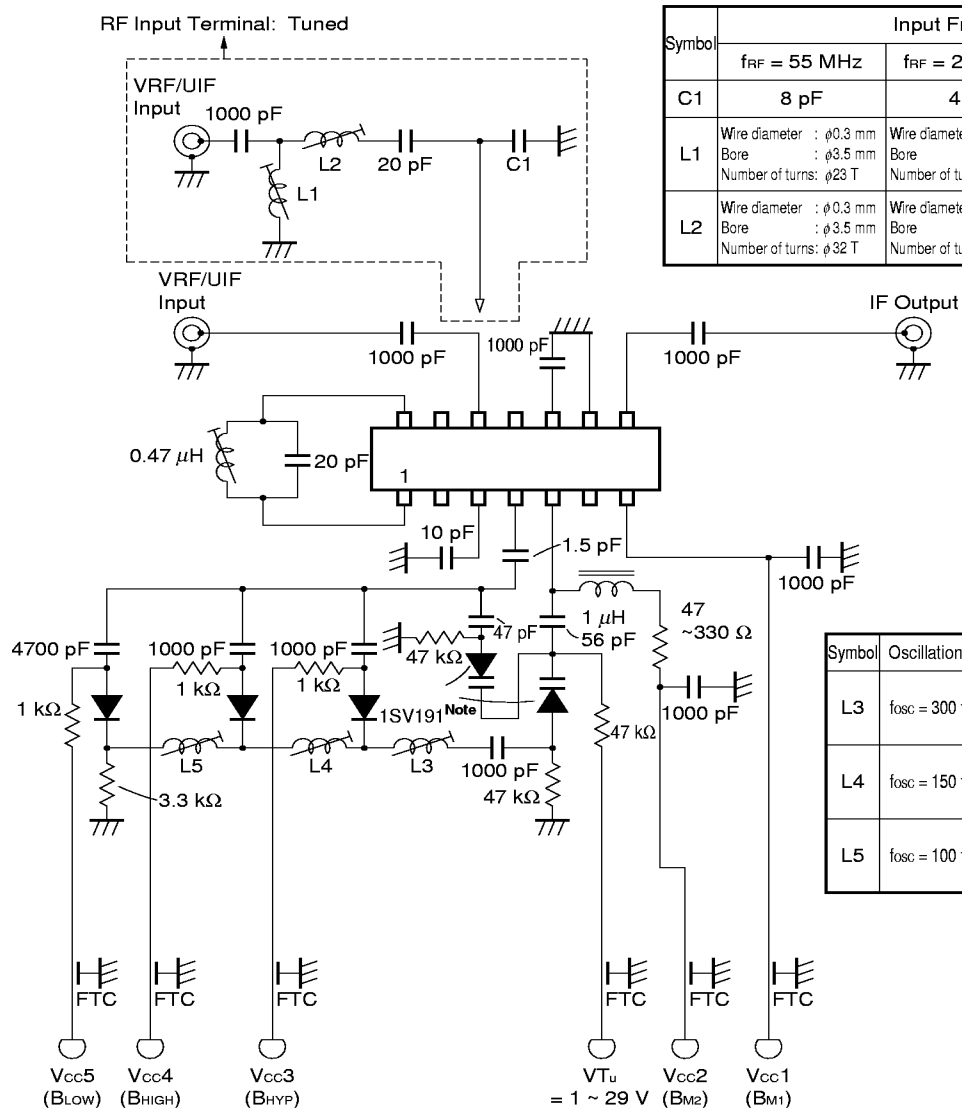


TEST CIRCUIT 1



When measuring circuit current with U/IF Amp, leave pin 5 open.

TEST CIRCUIT 2



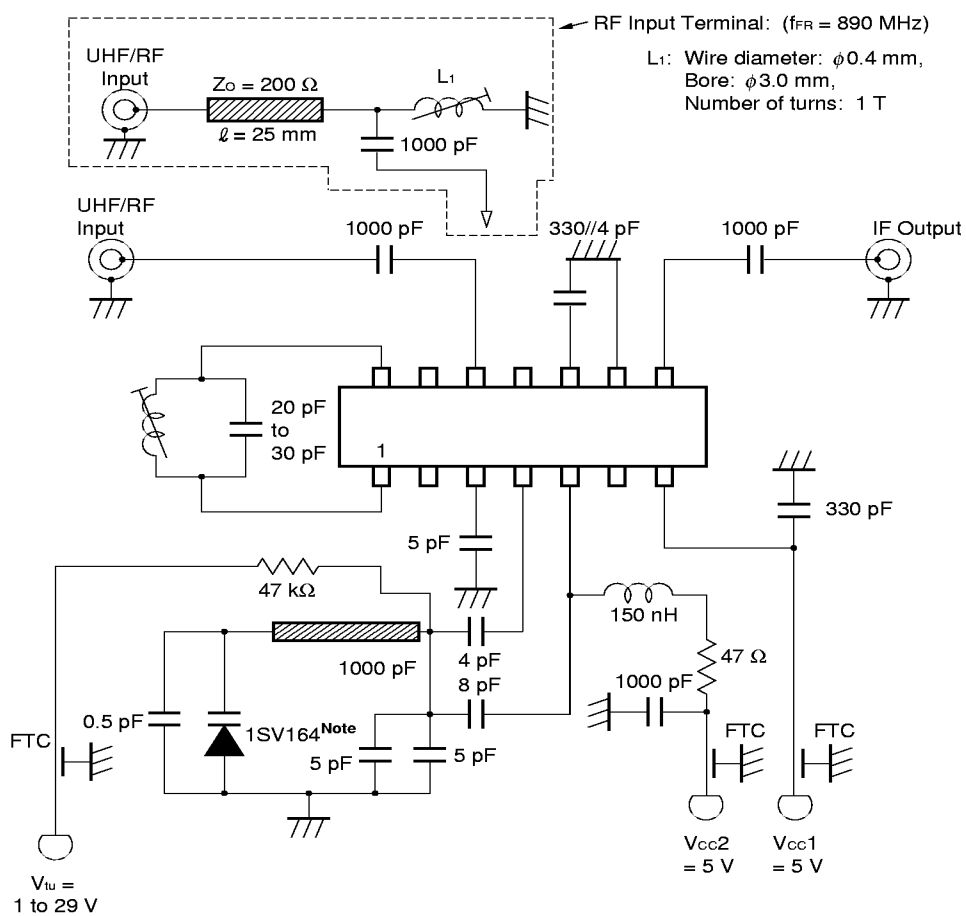
Symbol	Input Frequency		
	$f_{RF} = 55 \text{ MHz}$	$f_{RF} = 200 \text{ MHz}$	$f_{RF} = 470 \text{ MHz}$
C1	8 pF	4 pF	2 pF
L1	Wire diameter : $\phi 0.3 \text{ mm}$ Bore : $\phi 3.5 \text{ mm}$ Number of turns: $\phi 23 \text{ T}$	Wire diameter : $\phi 0.4 \text{ mm}$ Bore : $\phi 3.2 \text{ mm}$ Number of turns: $\phi 3 \text{ T}$	Wire diameter : $\phi 0.4 \text{ mm}$ Bore : $\phi 3.5 \text{ mm}$ Number of turns: $\phi 2 \text{ T}$
L2	Wire diameter : $\phi 0.3 \text{ mm}$ Bore : $\phi 3.5 \text{ mm}$ Number of turns: $\phi 32 \text{ T}$	Wire diameter : $\phi 0.3 \text{ mm}$ Bore : $\phi 4.0 \text{ mm}$ Number of turns: $\phi 7 \text{ T}$	Wire diameter : $\phi 0.5 \text{ mm}$ Bore : $\phi 3.5 \text{ mm}$ Number of turns: $\phi 2 \text{ T}$

Symbol	Oscillation Frequency	Coil used
L3	$f_{osc} = 300 \text{ to } 520 \text{ MHz}$	Wire diameter : $\phi 0.5 \text{ mm}$ Bore : $\phi 3.0 \text{ mm}$ Number of turns: $\phi 2 \text{ T}$
L4	$f_{osc} = 150 \text{ to } 300 \text{ MHz}$	Wire diameter : $\phi 0.4 \text{ mm}$ Bore : $\phi 2.5 \text{ mm}$ Number of turns: $\phi 3 \text{ T}$
L5	$f_{osc} = 100 \text{ to } 150 \text{ MHz}$	Wire diameter : $\phi 0.4 \text{ mm}$ Bore : $\phi 3.0 \text{ mm}$ Number of turns: $\phi 9 \text{ T}$

	Vcc1 (BM1)	Vcc2 (BM2)	Vcc3 (BHYP)	Vcc4 (BHIGH)	Vcc5 (BLOW)
V _{LOW}	5 V	5 V	OPEN	OPEN	5 V
V _{HIGH}	5 V	5 V	OPEN	5 V	OPEN
V _{HYPER}	5 V	5 V	5 V	OPEN	OPEN
U/IF	5 V	OPEN	OPEN	OPEN	OPEN

Note Our varactor diodes are discontinued.
For varactor diode, contact other supplier.

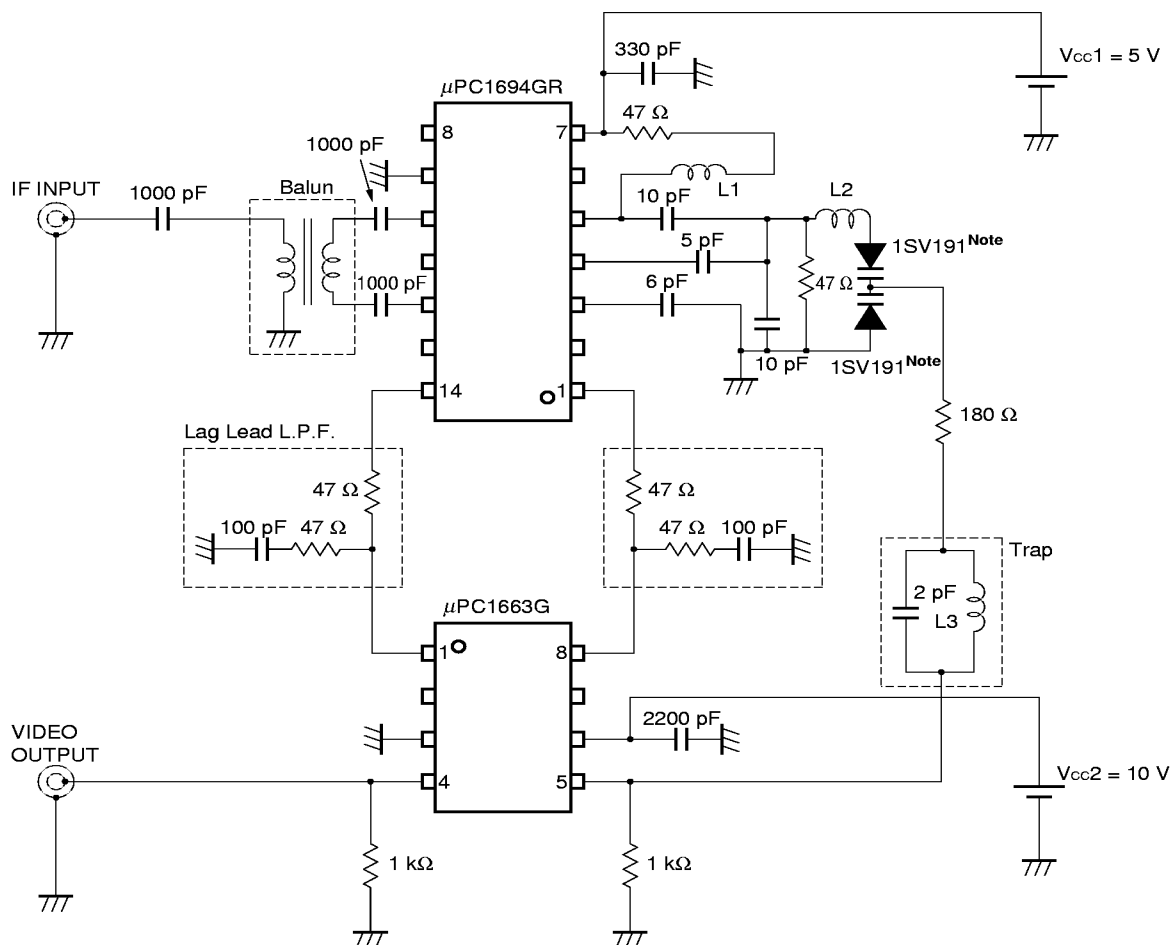
TEST CIRCUIT 3



Note Our varactor diodes are discontinued.
For varactor diode, contact other supplier.

APPLICATION CIRCUIT EXAMPLE 1

For FM demodulator (Example using μ PC1694GR and μ PC1663G)



L1: Wire diameter: ϕ 0.3 mm, Bore: ϕ 1.5 mm, Number of turns: 13 T
 L2: Wire diameter: ϕ 0.4 mm, Bore: ϕ 3.5 mm, Number of turns: 2 T
 L3: Wire diameter: ϕ 0.3 mm, Bore: ϕ 1.8 mm, Number of turns: 7 T
 Balun: TDK WBT5,5P5-C10129E

Note Our varactor diodes are discontinued.
 For varactor diode, contact other supplier.

For TV/VCR TUNER

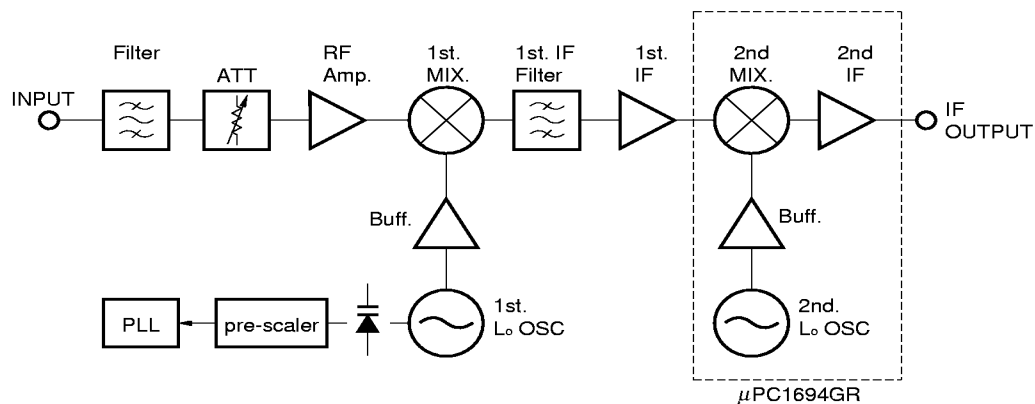
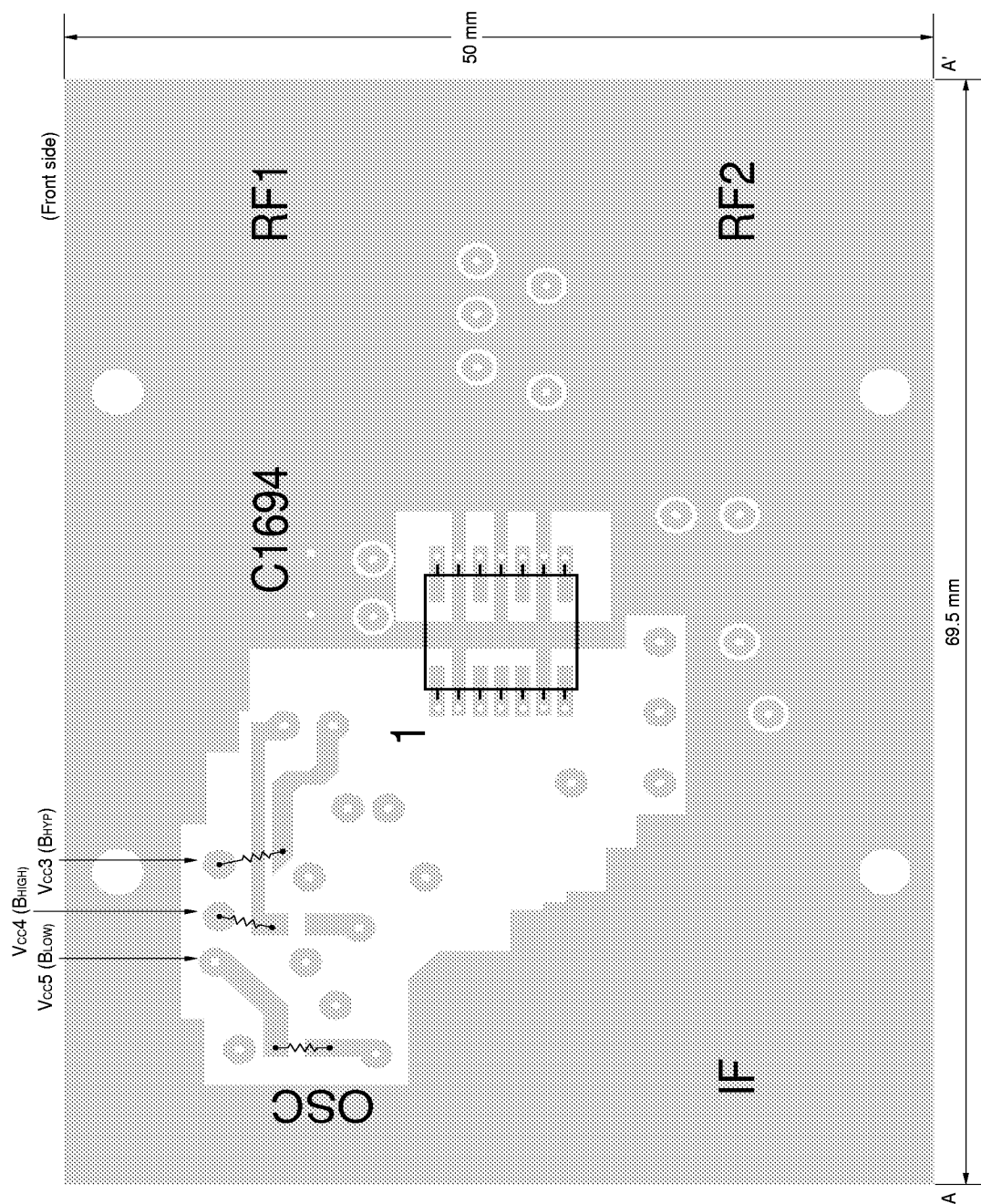
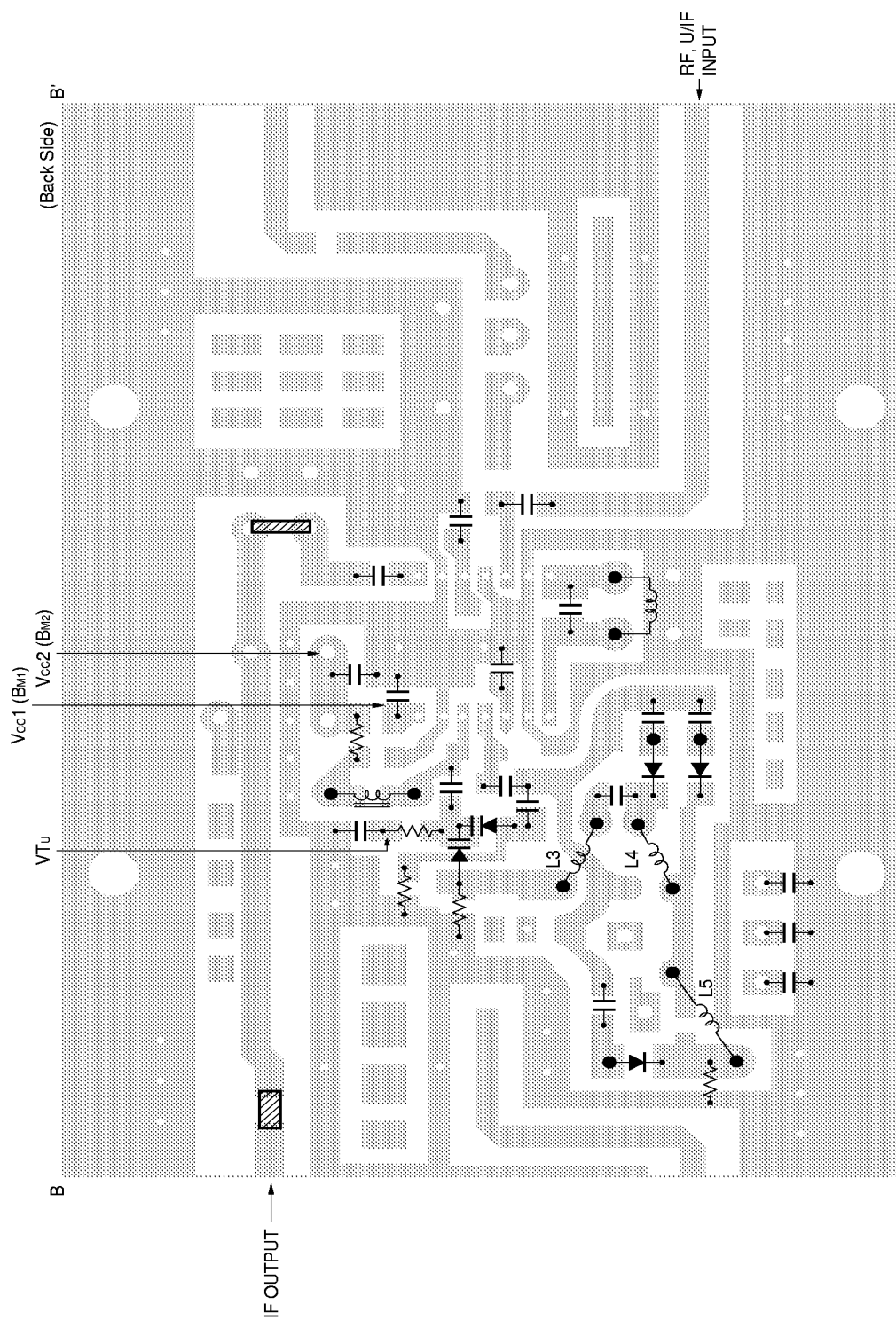


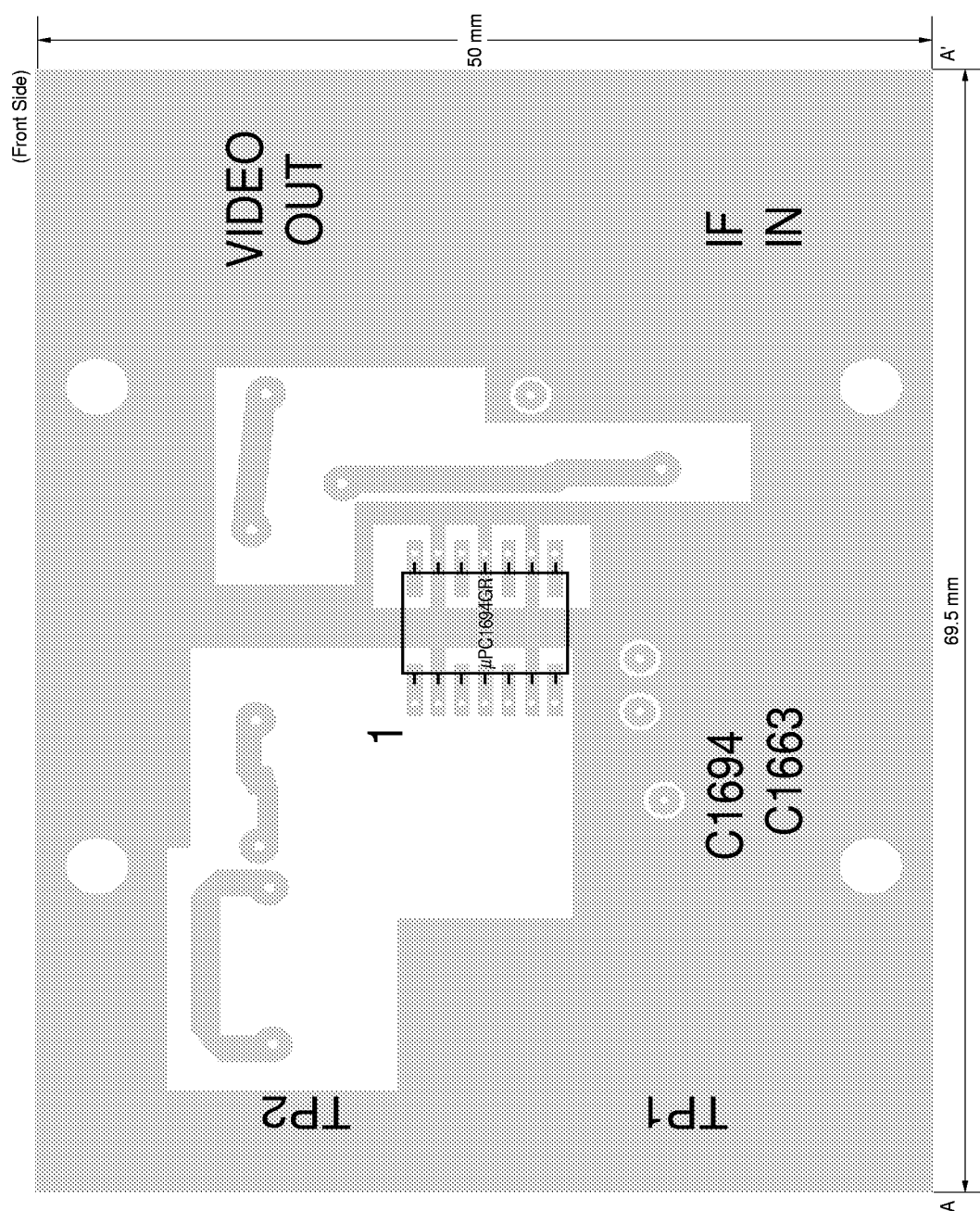
Illustration of The Application Circuit Example 2 Assembled on Evaluation Board

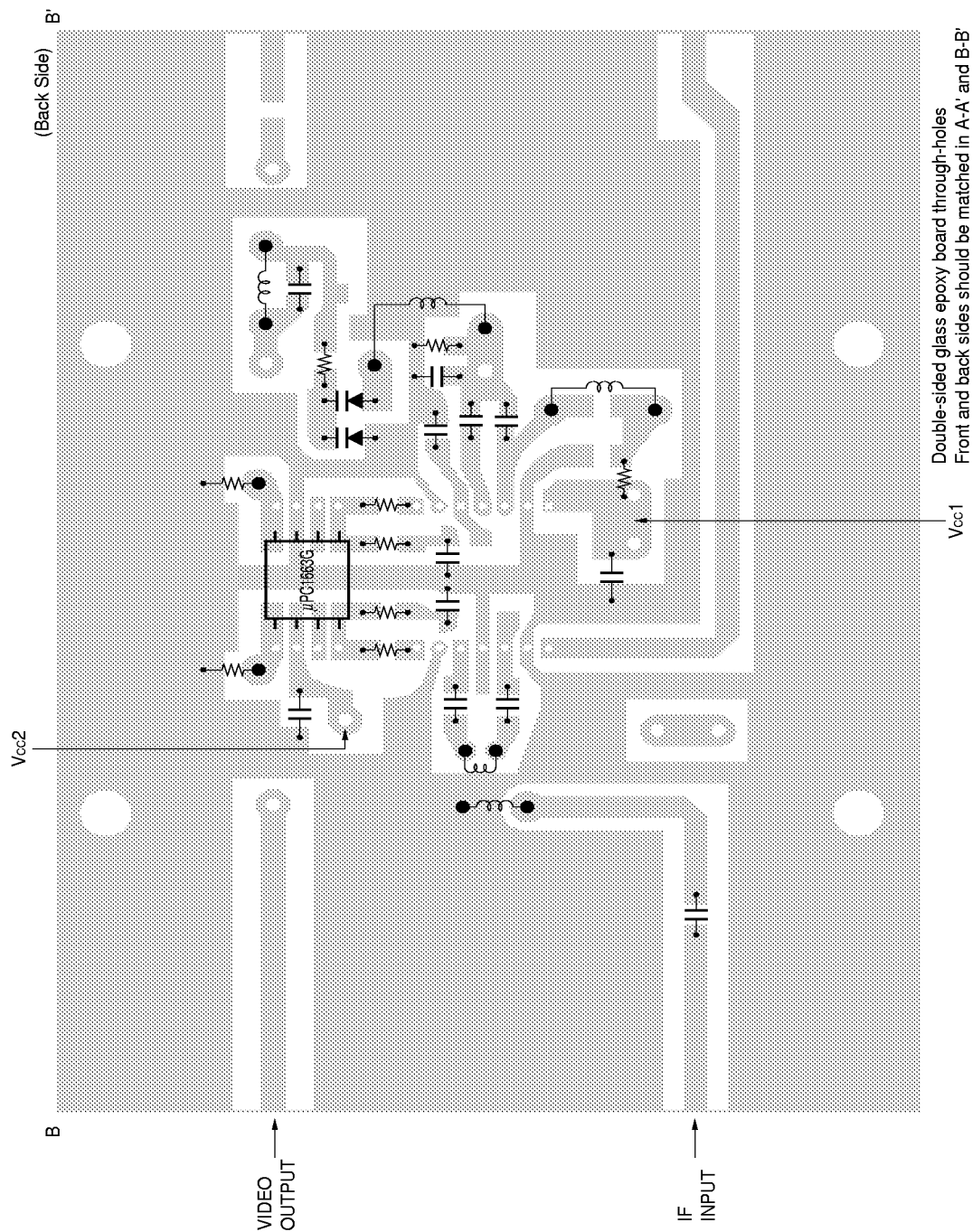




Double-sided glass epoxy board through-holes
 Front and back sides should be matched in A-A' and B-B'
 Hatched: short-circuited strip.

Illustration of The Application Circuit Example 1 Assembled on Evaluation Board

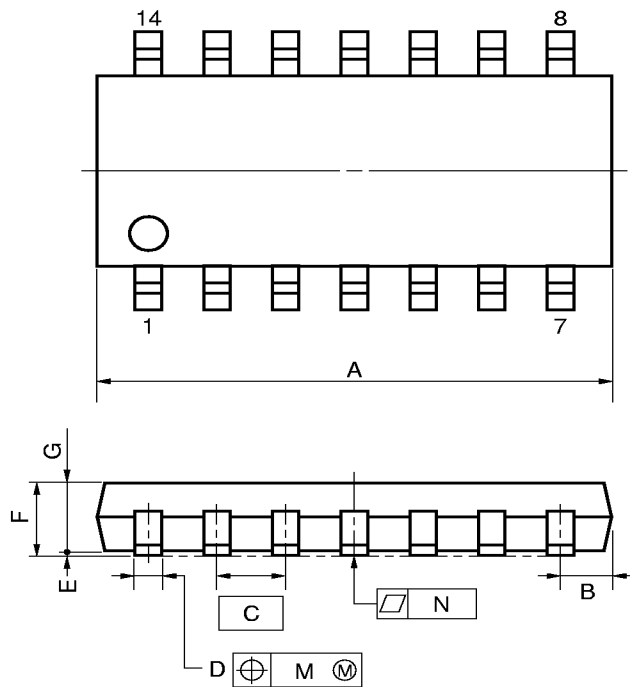




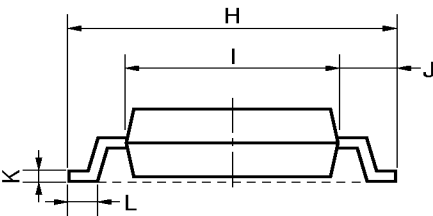
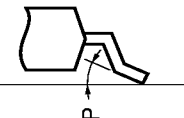
<Notes on Use>

- (1) Since this IC uses high frequency process, care is required against the excessive input of static electricity, etc.
- (2) Use the shortest possible wiring for the GND pin.
- (3) Use the widest possible earth pattern to avoid increase of ground impedance (because it may cause abnormal oscillation).
- (4) Insert a bypass capacitor for the V_{CC} pin (e.g., 1 000 pF, 2 200 pF, etc.)
- (5) Abnormal oscillation may occur depending on the values of the choke coil and floating capacitance. Therefore, insert a resistor between the power supply and choke coil. (See the application circuit example.)
- (6) Suppress the OSC injection level to prevent oscillation from saturating.
Adjust it by inserting a resistor to pin 2 in series. (See the application circuit example.)

14 PIN PLASTIC SOP (225 mil)



detail of lead end



NOTE
Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	10.46 MAX.	0.412 MAX.
B	1.42 MAX.	0.056 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40 ^{+0.10} _{-0.05}	0.016 ^{+0.004} _{-0.003}
E	0.1±0.1	0.004±0.004
F	1.8 MAX.	0.071 MAX.
G	1.49	0.059
H	6.5±0.3	0.256±0.012
I	4.4	0.173
J	1.1	0.043
K	0.15 ^{+0.10} _{-0.05}	0.006 ^{+0.004} _{-0.002}
L	0.6±0.2	0.024 ^{+0.008} _{-0.009}
M	0.12	0.005
N	0.10	0.004
P	3° ^{+7°} _{-3°}	3° ^{+7°} _{-3°}

S14GM-50-225B, C-4